



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI[®]

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Ι _D T _C = +25°C	
40V	6.5mΩ @ V _{GS} = 10V	100A	
407	9.8mΩ @ V _{GS} = 4.5V	80A	

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance.

Applications

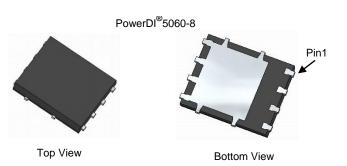
- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

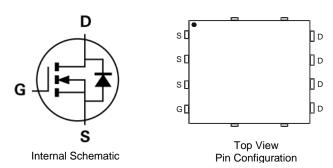
Features

- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.097 grams (Approximate)





Ordering Information (Note 4)

	Part Number	Case	Packaging	
DMTH4007LPS-13		PowerDI [®] 5060-8	2,500/Tape & Reel	
Notes: 1 FU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant All applicable RoHS exemptions applied				

EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D11=Manufacturer's Marking H4007LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015) WW = Week Code (01 to 53)

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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	15.5 13	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _C = +25°C T _C = +100°C	ID	100 80	А
Avalanche Current, L = 0.1mH	I _{AS}	20	А	
Avalanche Energy, L = 0.1mH		E _{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	55	°C/W
Total Power Dissipation (Note 6)	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	150	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						-	
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						-	
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		—	5.4	6.5		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.4	9.8	mΩ	V _{GS} = 4.5V, I _D = 20A	
Diode Forward Voltage	V _{SD}	—	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)						-	
Input Capacitance	Ciss	Ι	1,895	_		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	-	485	_	pF		
Reverse Transfer Capacitance	C _{rss}		20.9				
Gate Resistance	Rg	—	0.62	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	12.4	—		V _{DS} = 30V, I _D = 20A	
Total Gate Charge (V _{GS} = 10V)	Qq	—	29.1	—	nC		
Gate-Source Charge	Qgs	—	5.9	—	no		
Gate-Drain Charge	Q _{qd}	—	3.5	—			
Turn-On Delay Time	t _{D(ON)}	—	5.4	_			
Turn-On Rise Time	t _R	_	4.5	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_G = 3\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	—	16.2		ns		
Turn-Off Fall Time	tF	_	3.5				
Body Diode Reverse Recovery Time	t _{RR}	_	30.6	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	—	28.1	—	nC	IF = 20A, di/dt = 100A/µs	

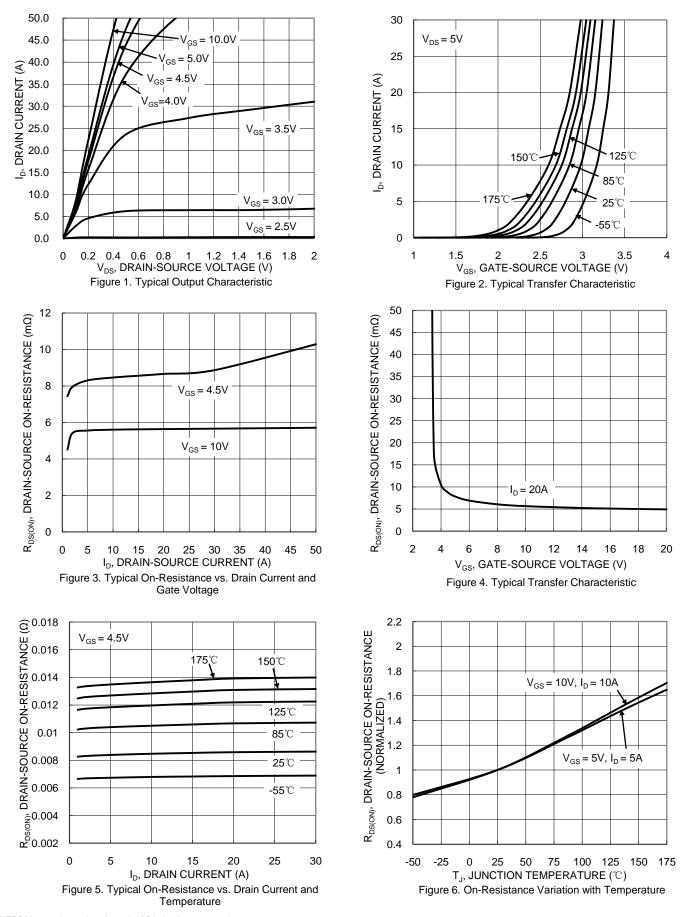
Notes:

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.



DMTH4007LPS



NEW PRODUCT

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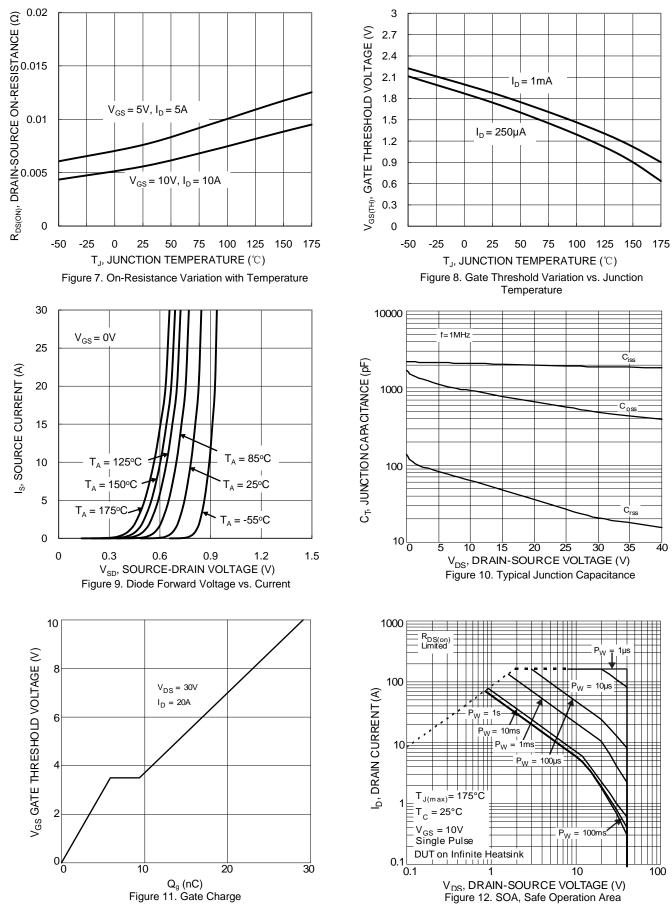
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EW PRODUCT

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DMTH4007LPS

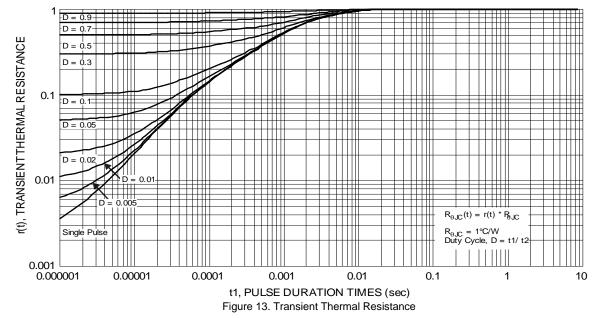


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DMTH4007LPS



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Package Outline

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

D Detail A D1 θ(4X) С A1 E1 E е + θ1 (4X) b(8X) e/2 ₿ b2 (4X) 踋 Ψ ZΠ DЗ ĸ $\overline{D2}$ b3 (4X) E3 E2 M M1 Detail A G

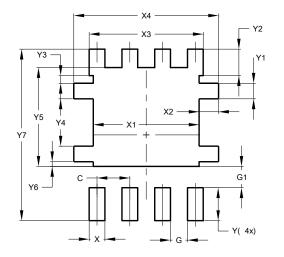
PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	.90 4.30			
ш		6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
e		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51		_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

PowerDI[®]5060-8

PowerDI[®]5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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